## PENDING CLAIMS

## 1-20. (Cancelled)

21. (Previously Presented) A electrode for an energy storage and conversion device, comprising

a substrate; and

a layer of an active material comprising a metal sulfide, metal selenide, or metal telluride, and having a thickness in the range from about 5 to about 114 microns deposited on the substrate, wherein the layer comprises greater than 95% of the active material.

## 22-23. (Cancelled)

- 24. (Original) The electrode of claim 21, wherein the active material is a metal sulfide.
- 25. (Previously Presented) The electrode of claim 21, wherein the active material is FeS<sub>2</sub>, CoS<sub>2</sub>, WS<sub>2</sub>, NiS<sub>2</sub>, or MoS<sub>2</sub>.
  - 26. (Original) The method of claim 21, wherein the active material is FeS<sub>2</sub>,
- 27. (Previously Presented) The electrode of claim 21, wherein the active material is microstructured.
- 28. (Previously Presented) The electrode of claim 21, wherein the active material is nanostructured.

29-40. (Cancelled)



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(Previously Presented) An electrode for an energy storage and conversion device, comprising

a substrate; and

a layer of an active material comprising FeS2, CoS2, WS2, NiS2, MoS2, metal selenide, or metal telluride, and having a thickness in the range from about 5 to about 114 microns deposited on the substrate, wherein the layer comprises greater than 95% of the active material.

- 42. (Previously Presented) The electrode of claim 41, wherein the active material is FeS2.
- 43. (Previously Presented) The electrode of claim 41, wherein the active material is microstructured.
- 44. (Previously Presented) The electrode of claim 41, wherein the active material is nanostructured.
- (Previously Presented) An electrode for an energy storage and conversion device, comprising
  - a substrate; and
- a layer of an active material having a thickness in the range from about 5 to about 114 microns comprising a metal sulfide, metal selenide, or metal telluride deposited on the substrate by a thermal spray method comprising providing a feedstock mixture comprising an effective quantity of a source of elemental sulfur and a metal sulfide, an effective quantity of a source of elemental selenium and a metal selenide, or an effective quantity of a source of elemental tellurium and a metal telluride and thermally spraying the feedstock mixture onto the substrate.

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- (Previously Presented) The electrode of claim 45, wherein the active material 46. is a metal sulfide.
- (Previously Presented) The electrode of claim 45, wherein the active material 47. is FeS<sub>2</sub>, CoS<sub>2</sub>, WS<sub>2</sub>, NiS<sub>2</sub>, or MoS<sub>2</sub>.
- (Previously Presented) The electrode of claim 45, wherein the active material is microstructured.
- (Previously Presented) The electrode of claim 45, wherein the active material 49. is nanostructured.
- (Previously Presented) An electrode produced by the process of: 50. thermally spraying a feedstock mixture onto a substrate to produce a film of an active material having a thickness of about 1 to about 1000 microns, wherein the feedstock material comprises an effective quantity of a source of elemental sulfur and a metal sulfide active material, an effective quantity of a source of elemental selenium and a metal selenide active material, or an effective quantity of a source of a elemental tellurium and a metal telluride active material.
- (Previously Presented) The electrode of Claim 50, wherein the feedstock 51. mixture comprises a source of elemental sulfur and metal sulfide.
- (Previously Presented) The electrode of Claim 51, wherein the metal sulfide is 52.  $FeS_2$ ,  $CoS_2$ ,  $WS_2$ ,  $NiS_2$ , or  $MoS_2$ .
- (Previously Presented) The electrode of Claim 50, wherein the active material is microstructured.
- (Previously Presented) The electrode of Claim 50, wherein the active material 54. is nanostructured.